

Silicon NPN Power Transistors

2SD200

DESCRIPTION

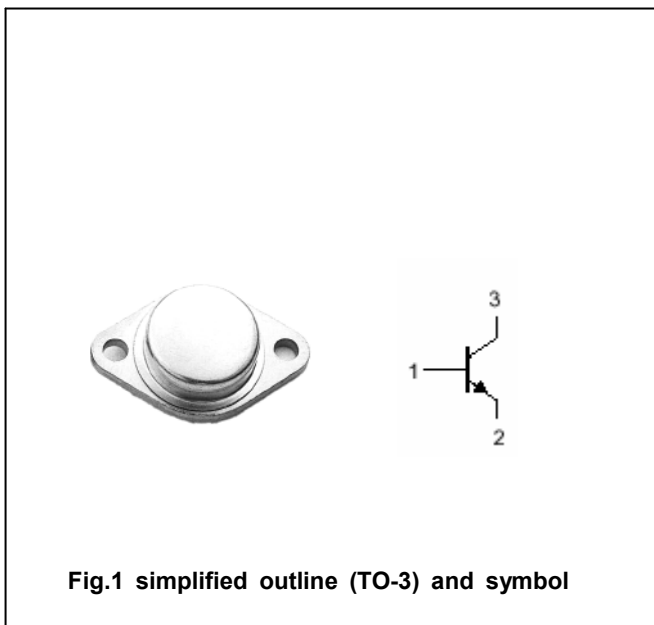
- With TO-3 package
- High voltage ,high reliability
- Wide area of safe operation

APPLICATIONS

- For color TV horizontal output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		2.5	A
P_C	Collector power dissipation	$T_C = 90 \square$	10	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~150	$\square$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=100mA$; $I_B=0$	600			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=2A$; $I_B=0.6A$			8.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=2A$; $I_B=0.6A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=500V$; $I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			100	μA
h_{FE-1}	DC current gain	$I_C=0.5A$; $V_{CE}=5V$	8			
h_{FE-2}	DC current gain	$I_C=2A$; $V_{CE}=5V$	2.5			

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PACKAGE OUTLINE

